

ABSTRACT OF THE DISCLOSURE

A semiconductor memory comprises: a first conductivity type semiconductor substrate and one or more memory cells constituted of an island-like semiconductor layer, 5 a charge storage layer and a control gate, the charge storage layer and the control gate being formed to entirely or partially encircle a sidewall of the island-like semiconductor layer, wherein at least one of said one or more memory cells is electrically insulated from the semiconductor substrate.

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